

MOSFET – Dual, N-Channel, Shielded Gate, POWERTRENCH®

100 V, 39 A, 10.5 mΩ

FDMD86100

General Description

This package integrates two N-Channel devices connected internally in common-source configuration and incorporates Shielded Gate technology. This enables very low package parasitics and optimized thermal path to the common source pad on the bottom. Provides a very small footprint (5 x 6 mm) for higher power density.

Features

- Common Source Configuration to Eliminate PCB Routing
- Large Source Pad on Bottom of Package for Enhanced Thermals
- Shielded Gate MOSFET Technology
- Max $r_{DS(on)}$ = 10.5 mΩ at $V_{GS} = 10\text{ V}$, $I_D = 10\text{ A}$
- Max $r_{DS(on)}$ = 17.3 mΩ at $V_{GS} = 6\text{ V}$, $I_D = 7.8\text{ A}$
- Ideal for Flexible Layout in Secondary Side Synchronous Rectification
- 100% UIL tested
- This Device is Pb-Free, Halide Free and is RoHS Compliant

Applications

- Isolated DC-DC Synchronous Rectifiers
- Common Ground Load Switches

MOSFET MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

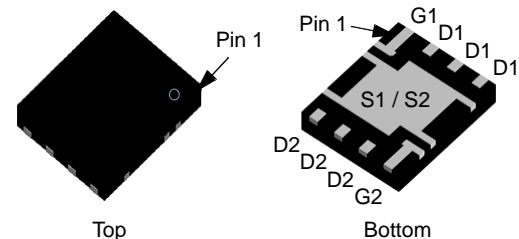
Symbol	Parameter	Ratings	Unit
V_{DS}	Drain to Source Voltage	100	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current – Continuous $T_C = 25^\circ\text{C}$ (Note 5) – Continuous $T_C = 100^\circ\text{C}$ (Note 5) – Continuous $T_A = 25^\circ\text{C}$ (Note 1a) – Pulsed (Note 4)	39 24 10 299	A
E_{AS}	Single Pulse Avalanche Energy (Note 3)	337	mJ
P_D	Power Dissipation $T_C = 25^\circ\text{C}$ $T_A = 25^\circ\text{C}$ (Note 1a)	33 2.2	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, unless otherwise noted)

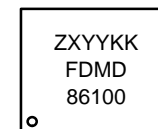
Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.7	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	55	

V_{DS}	$r_{DS(on)}$ MAX	I_D MAX
100 V	10.5 mΩ @ 10 V	39 A
	17.3 mΩ @ 6 V	



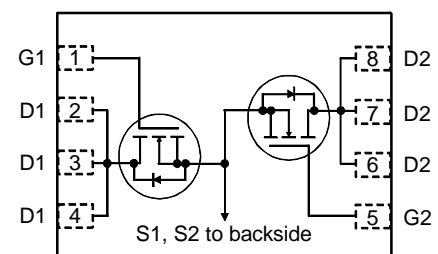
QFN8 5X6, 1.27P
(Power 5 x 6)
CASE 483AS

MARKING DIAGRAM



ZZ = Assembly Site Code
X = Year Code
YY = Weekly Code
KK = Lot Code
FDMD86100 = Device Code

PIN ASSIGNMENT



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

FDMD86100

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

B _V DSS	Drain to Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0 V	100	–	–	V
$\frac{\Delta B_{V_{DSS}}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, referenced to 25°C	–	7	–	mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 80 V, V _{GS} = 0 V	–	–	1	μA
I _{GSS}	Gate to Source Leakage Current	V _{GS} = ±20 V, V _{DS} = 0 V	–	–	±100	nA

ON CHARACTERISTICS

V _{GS(th)}	Gate to Source Threshold Voltage	V _{GS} = V _{DS} , I _D = 250 μA	2.0	3.0	4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I _D = 250 μA, referenced to 25°C	–	–10	–	mV/°C
r _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 10 A	–	7.8	10.5	mΩ
		V _{GS} = 6 V, I _D = 7.8 A	–	12	17.3	
		V _{GS} = 10 V, I _D = 10 A, T _J = 125°C	–	14.5	19.5	
g _{FS}	Forward Transconductance	V _{DD} = 5 V, I _D = 10 A	–	26	–	S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz	–	1469	2060	pF
C _{oss}	Output Capacitance		–	321	450	pF
C _{rss}	Reverse Transfer Capacitance		–	12	20	pF
R _g	Gate Resistance		0.1	1.3	3.3	Ω

SWITCHING CHARACTERISTICS

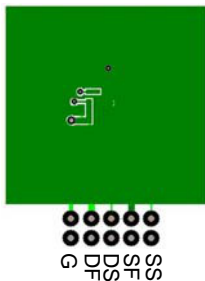
t _{d(on)}	Turn-On Delay Time	V _{DD} = 50 V, I _D = 10 A, V _{GS} = 10 V, R _{GEN} = 6 Ω	–	13	23	ns
t _r	Rise Time		–	4.3	10	ns
t _{d(off)}	Turn-Off Delay Time		–	18	32	ns
t _f	Fall Time		–	4.1	10	ns
Q _{g(TOT)}	Total Gate Charge		V _{GS} = 0 V to 10 V, V _{DD} = 50 V, I _D = 10 A	–	21	30
	Total Gate Charge	V _{GS} = 0 V to 6 V, V _{DD} = 50 V, I _D = 10 A	–	13	18	nC
Q _{gs}	Gate to Source Charge	V _{DD} = 50 V, I _D = 10 A	–	6.6	–	nC
Q _{gd}	Gate to Drain "Miller" Charge		–	4.1	–	nC

DRAIN-SOURCE CHARACTERISTICS

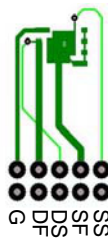
V _{SD}	Source to Drain Diode Forward Voltage	V _{GS} = 0 V, I _S = 10 A (Note 2)	–	0.8	1.3	V
		V _{GS} = 0 V, I _S = 2 A (Note 2)	–	0.7	1.2	
t _{rr}	Reverse Recovery Time	I _F = 10 A, di/dt = 100 A/μs	–	46	74	ns
Q _{rr}	Reverse Recovery Charge		–	46	74	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- R_{θJA} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{θCA} is determined by the user's board design.



a. 55°C/W when mounted on a 1 in² pad of 2 oz copper



b. 125°C/W when mounted on a minimum pad of 2 oz copper

- Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
- E_{AS} of 337 mJ is based on starting T_J = 25°C, L = 3 mH, I_{AS} = 15 A, V_{DD} = 100 V, V_{GS} = 10 V. 100% tested at L = 0.1 mH, I_{AS} = 47 A.
- Pulse I_d refers to Figure 11 SOA graph for details.
- Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise noted)

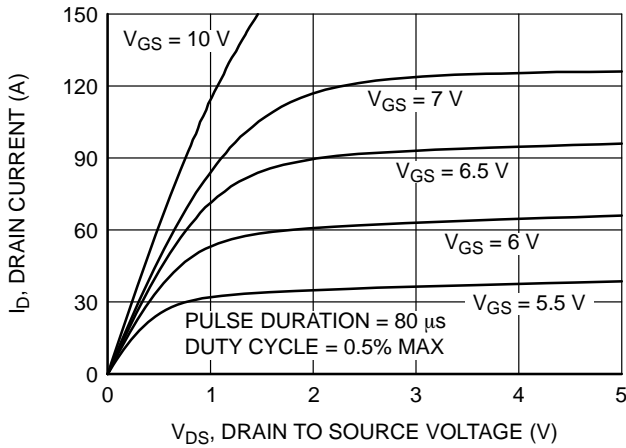


Figure 1. On-Region Characteristics

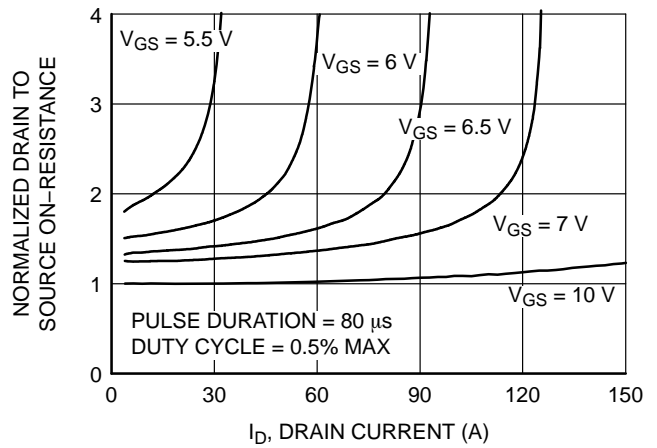


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

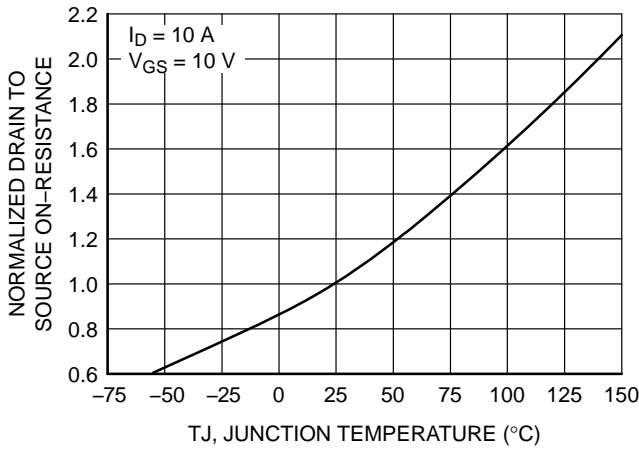


Figure 3. Normalized On-Resistance vs. Junction Temperature

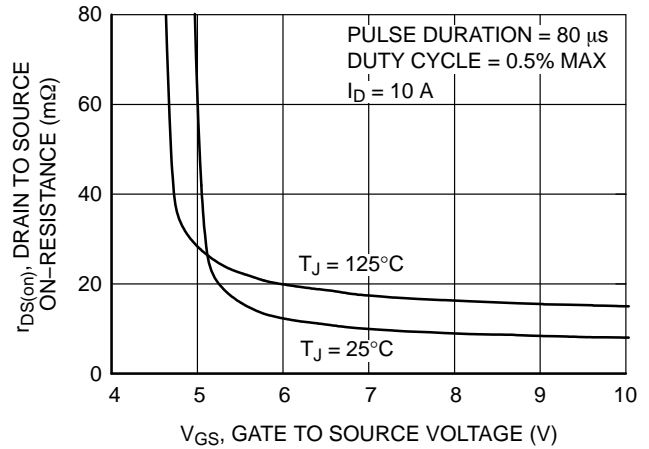


Figure 4. On-Resistance vs. Gate to Source Voltage

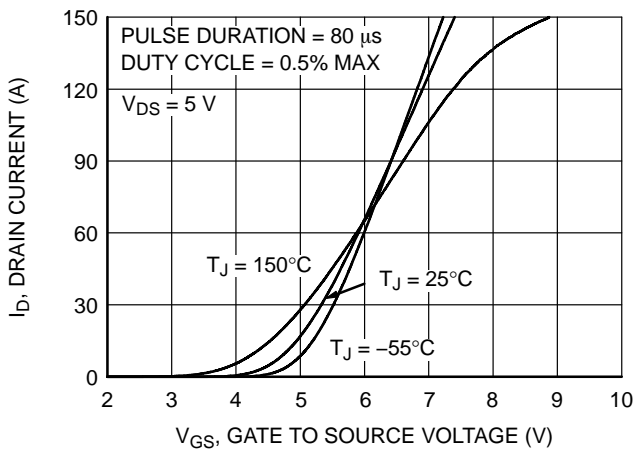


Figure 5. Transfer Characteristics

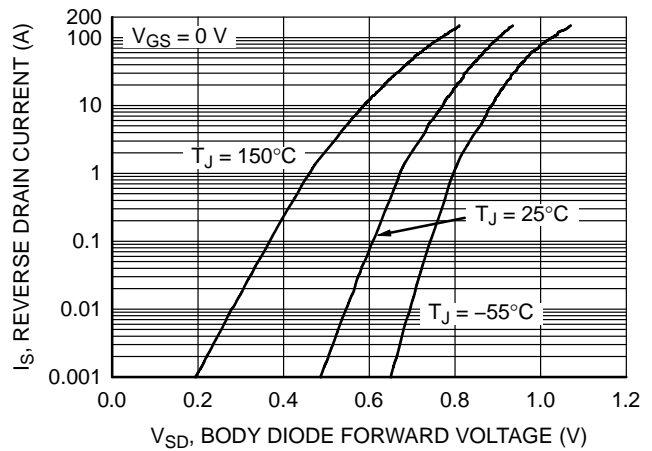


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise noted) (continued)

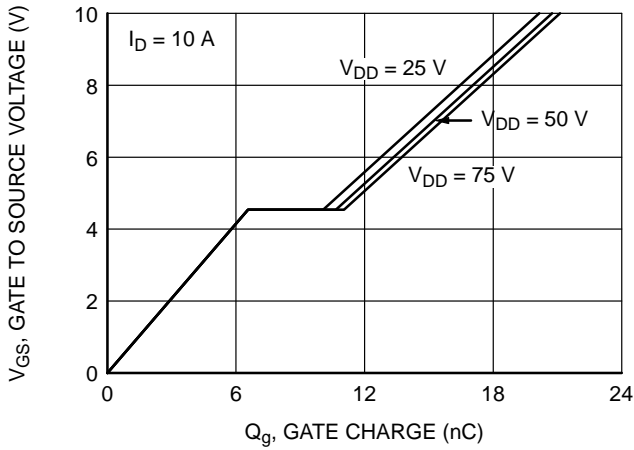


Figure 7. Gate Charge Characteristics

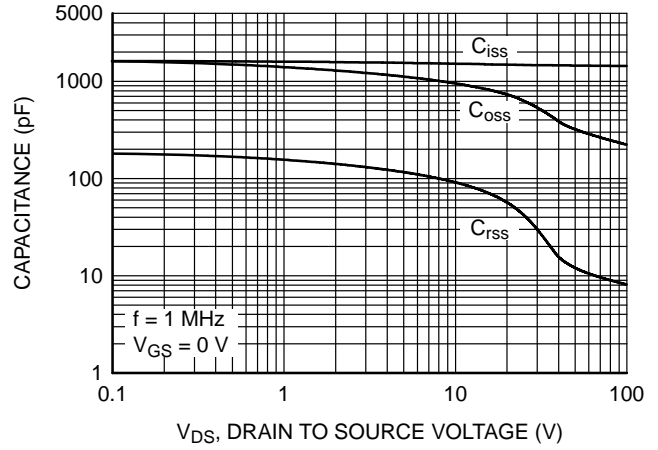


Figure 8. Capacitance vs. Drain to Source Voltage

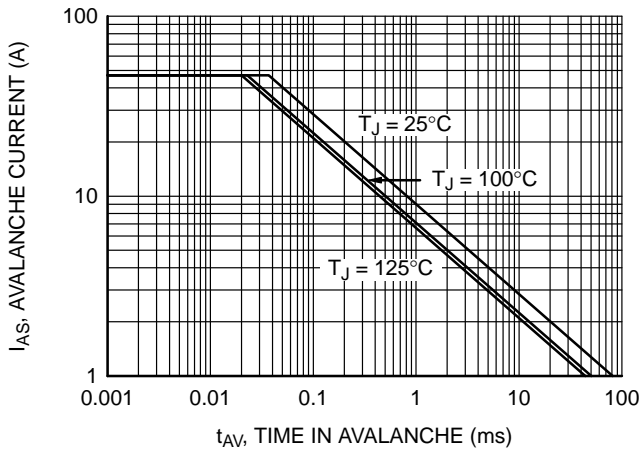


Figure 9. Unclamped Inductive Switching Capability

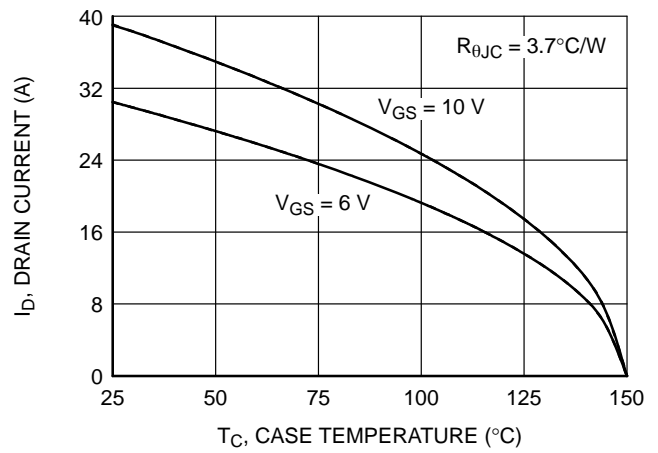


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

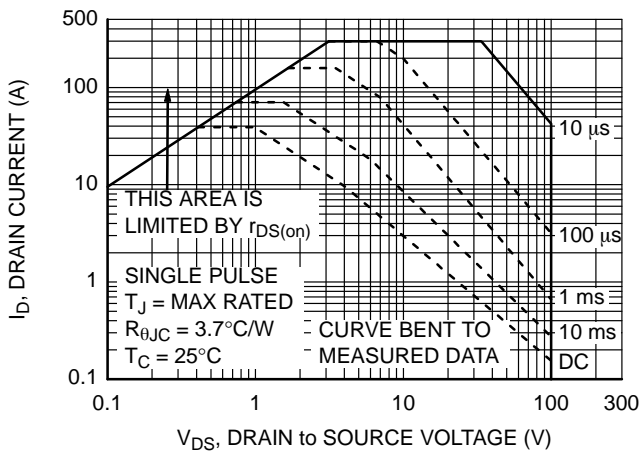


Figure 11. Forward Bias Safe Operating Area

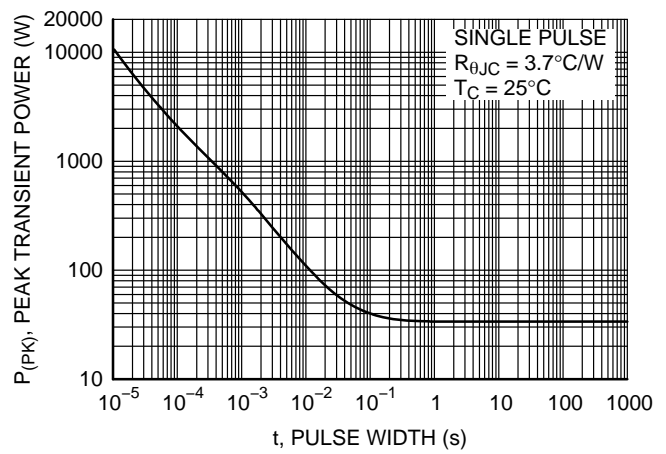


Figure 12. Single Pulse Maximum Power Dissipation

FDMD86100

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise noted) (continued)

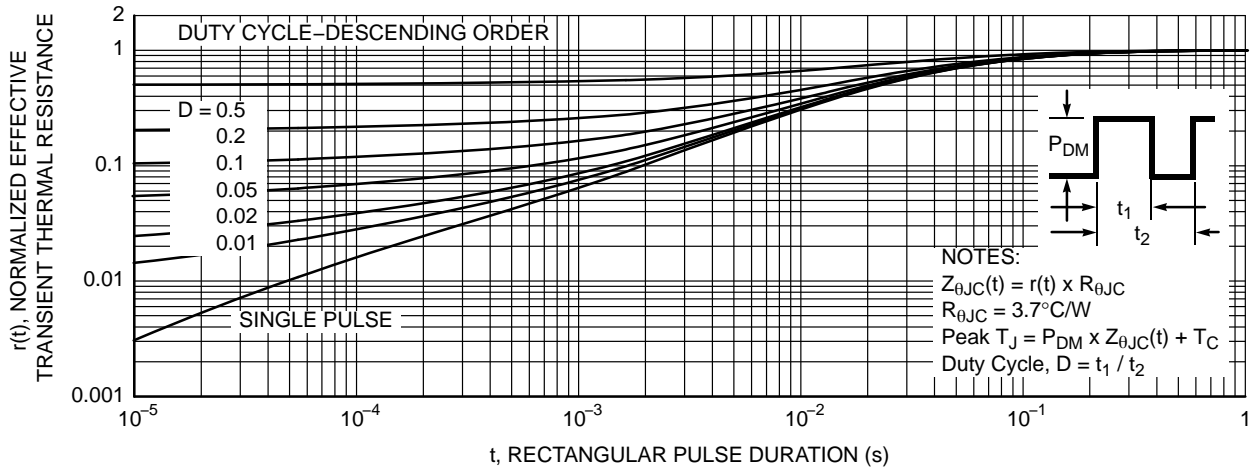


Figure 13. Junction-to-Case Transient Thermal Response Curve

PACKAGE MARKING AND ORDERING INFORMATION

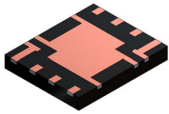
Device	Device Marking	Package	Reel Size	Tape Width	Shipping†
FDMD86100	FDMD86100	PQFN8 5X6, 1.27P (Power 5 x 6) (Pb-Free, Halide Free)	13"	12 mm	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®

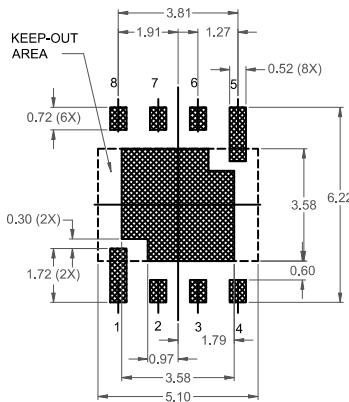
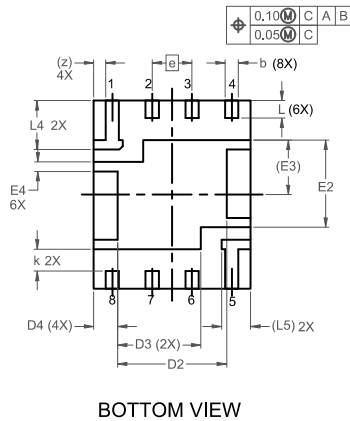
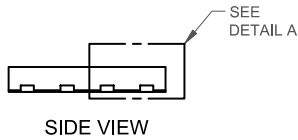
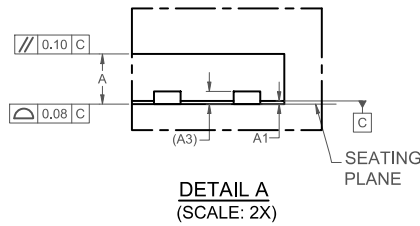
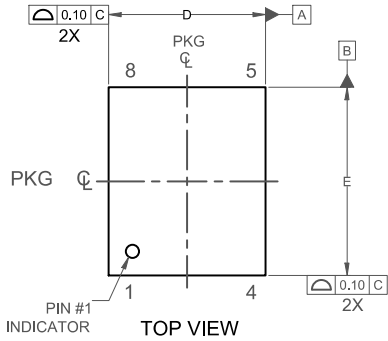


PQFN8 5X6, 1.27P CASE 483AS ISSUE A

DATE 17 MAY 2021

NOTES:

- A) PACKAGE REFERENCE :
TO JEDEC REGISTRATION, MO-240B, VARIATION AA.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH.
MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- D) DIMENSIONING AND TOLERANCING PER ASME
Y14.5M-2009
- E) IT IS RECOMMENDED TO HAVE NO
TRACES OR VIAS WITHIN THE KEEP-OUT AREA



*FOR ADDITIONAL INFORMATION ON OUR
PB-FREE STRATEGY AND SOLDERING
DETAILS, PLEASE DOWNLOAD THE ON
SEMICONDUCTOR SOLDERING AND
MOUNTING TECHNIQUES REFERENCE
MANUAL, SOLDERRM/D.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	0.00	-	0.05
b	0.37	0.42	0.47
A3	0.20 REF		
D	4.90	5.00	5.10
D2	3.38	3.48	3.58
D3	2.55	2.65	2.75
D4	0.66	0.76	0.86
E	5.90	6.00	6.10
E2	2.68	2.78	2.88
E3	1.74 REF		
E4	0.25	0.30	0.35
e	1.27 BSC		
k	0.60	0.70	0.80
L	0.46	0.56	0.66
L4	1.46	1.56	1.66
L5	0.82	0.92	1.02
z	0.39 REF		

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DESCRIPTION:	PQFN8 5X6, 1.27P	PAGE 1 OF 1

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